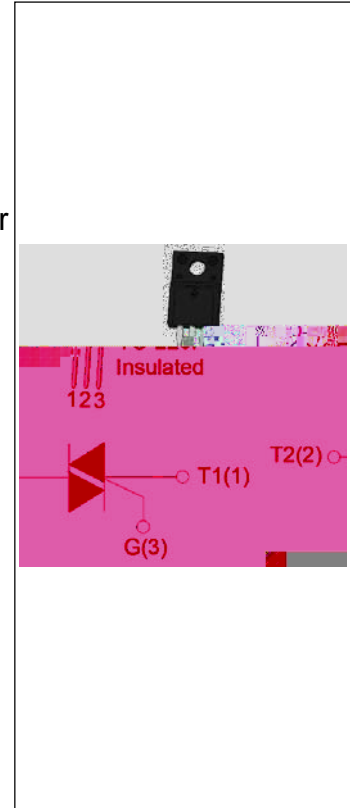




JST16F-1200CW 16A TRIAC

Rev.A.1.1

The JST16F-1200CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST16F-1200CW snubberless triac is especially recommended for use on inductive loads. By using an external plastic package, JST16F-1200CW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	1200	V
$I_{GT} / /$	35/35/35	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	1200	V
Non repetitive peak current ($t_{peak} = 20ms, T_j=25^\circ C$)	I_{Tzrrm}	160	A
Non repetitive peak current ($t_{peak} = 16.6ms, T_j=25^\circ C$)	I_{Tzrrm}	176	A
Surge current ($t_{peak} = 10ms, T_j=25^\circ C$)	I^2t	128	A^2s
Critical rate of change of current ($I_{GT}=2, f=100Hz, T_j=125^\circ C$)	di/dt	100	$A/\mu s$
Peak gate current ($T_j=125^\circ C$)	I_g	4	A
Average power dissipation ($T_j=125^\circ C$)	PAV)		W

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
I_H	$I_T=500mA$		MAX.	40	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$		MIN.	400	V/ μs
(dI/dt)c	(dV/dt)c=20V/ μs $T_j=125$		MIN.	10	A/ms
t_{on}	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	7	μs
t_{off}				50	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=22.5A t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.77	V
R_D	Dynamic resistance	$T_j=125$	32	m
I_{DRM} I_{RRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	10	μA

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FIG.1: Maximum power dissipation versus RMS on-state current

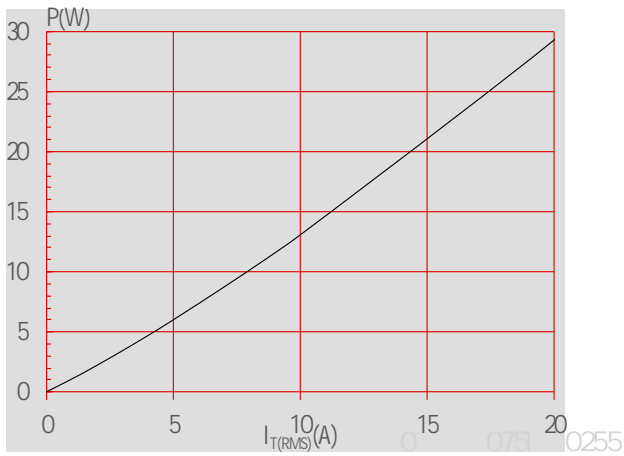


FIG.2: RMS on-state current versus case temperature

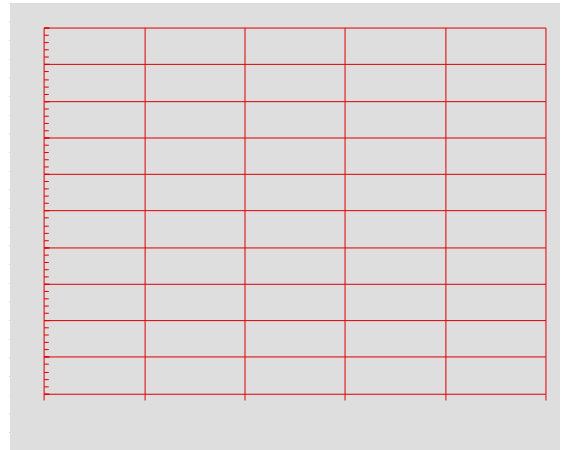
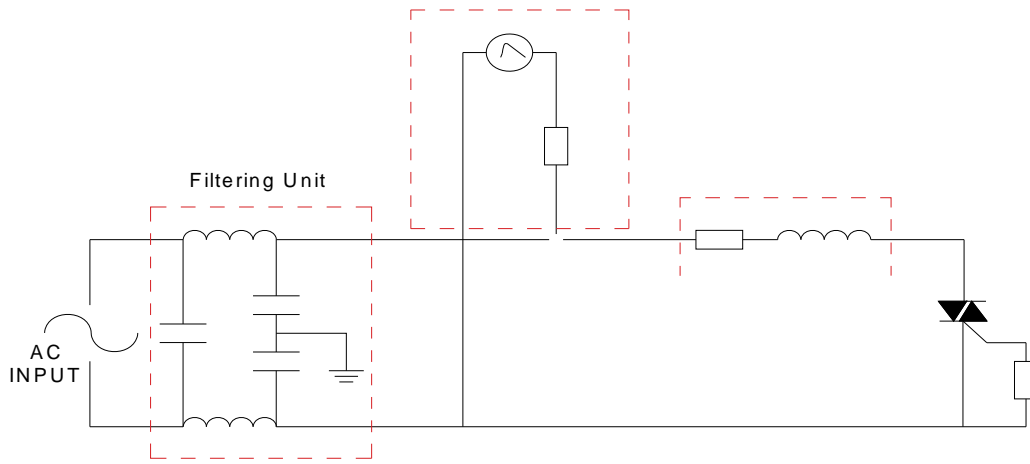


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





Information furnished in this document is believed to be accurate and reliable. However,
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